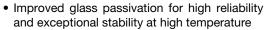


# Medium Power Phase Control Thyristors (Stud Version), 25 A



PRODUCT SUMMARY				
Package	TO-208AA (TO-48)			
Diode variation	Single SCR			
I <sub>T(AV)</sub>	25 A			
V <sub>DRM</sub> /V <sub>RRM</sub>	100 V, 1200 V			
V <sub>TM</sub>	1.70 V			
I <sub>GT</sub>	60 mA			
T <sub>J</sub>	-65 °C to +125 °C			

#### **FEATURES**





- High dl/dt and dV/dt capabilities
- Standard package
- · Low thermal resistance
- · Metric threads version available
- Types up to 1200 V V<sub>DRM</sub>/V<sub>RRM</sub>
- Designed and qualified for industrial and consumer level
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

#### **TYPICAL APPLICATIONS**

- Medium power switching
- · Phase control applications

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
1		25	А		
I <sub>T(AV)</sub>	T <sub>C</sub>	85	°C		
I <sub>T(RMS)</sub>		40	A		
I <sub>TSM</sub>	50 Hz	420	Δ.		
	60 Hz	440	A		
101	50 Hz	867	A <sup>2</sup> s		
I <sup>2</sup> t	60 Hz	790	A-S		
V <sub>DRM</sub> /V <sub>RRM</sub>		100 to 1200	V		
tq	Typical	110	μs		
TJ		-65 to +125	°C		

#### **ELECTRICAL SPECIFICATIONS**

VOLTAGE RATINGS							
TYPE NUMBER	VOLTAGE CODE	V <sub>DRM</sub> /V <sub>RRM</sub> , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE <sup>(1)</sup> V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK VOLTAGE <sup>(2)</sup> V	$\begin{aligned} I_{DRM}/I_{RRM} & \text{MAXIMUM} \\ \text{AT T}_{J} = T_{J} & \text{MAXIMUM} \\ & \text{mA} \end{aligned}$			
	10	100	150	20			
	20	200	300				
	40	400	500				
VS-25RIA	60	600	700	10			
	80	800	900	10			
	100	1000	1100				
	120	1200	1300				

#### Notes

<sup>(1)</sup> Units may be broken over non-repetitively in the off-state direction without damage, if dl/dt does not exceed 20 A/µs

<sup>(2)</sup> For voltage pulses with  $t_p \le 5$  ms



<b>ABSOLUTE MAXIMUM RAT</b>	INGS					
PARAMETER	SYMBOL		TEST CONE	DITIONS	VALUES	UNITS
Maximum average on-state current at case temperature	I <sub>T(AV)</sub>	180° sinusoi	dal conduction		25 85	A °C
Maximum RMS on-state current	1				40	A
Maximum RMS on-State current	I <sub>T(RMS)</sub>			I		A
		t = 10 ms	No voltage		420	
Maximum peak, one-cycle	<b>.</b>	t = 8.3 ms	reapplied		440	^
non-repetitive surge current	I <sub>TSM</sub>	t = 10 ms	100 % V <sub>RRM</sub>		350	A
		t = 8.3 ms	reapplied	Sinusoidal half wave,	370	
		t = 10 ms	No voltage	initial T <sub>J</sub> = T <sub>J</sub> maximum	867	A <sup>2</sup> s
Maximum I <sup>2</sup> t for fusing	l <sup>2</sup> t	t = 8.3 ms	reapplied		790	
		t = 10 ms	100 % V <sub>RRM</sub> reapplied		615	
		t = 8.3 ms			560	
Maximum I²√t for fusing	I²√t		t = 0.1 to 10 ms, no voltage reapplied, T <sub>J</sub> = T <sub>J</sub> maximum		8670	A²√s
Low level value of threshold voltage	V <sub>T(TO)1</sub>	(16.7 % x $\pi$ x $I_{T(AV)}$ < I < $\pi$ x $I_{T(AV)}$ ), $T_J = T_J$ maximum		0.99	V	
High level value of threshold voltage	V <sub>T(TO)2</sub>	$(I > \pi \times I_{T(AV)})$	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$		1.40	v
Low level value of on-state slope resistance	r <sub>t1</sub>	(16.7 % x $\pi$ x $I_{T(AV)}$ < I < $\pi$ x $I_{T(AV)}$ ), $T_J = T_J$ maximum		10.1		
High level value of on-state slope resistance	r <sub>t2</sub>	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$		5.7	mΩ	
Maximum on-state voltage	$V_{TM}$	I <sub>pk</sub> = 79 A, T <sub>J</sub> = 25 °C		1.70	V	
Maximum holding current	I <sub>H</sub>	T 05.00 a	T <sub>J</sub> = 25 °C, anode supply 6 V, resistive load		130	mA
Latching current	ΙL	1 J = 25 °C, 8			200	

SWITCHING					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
	$V_{DRM} \leq 600 \; V$				
of turned-on current $V_{DRM} \le 10$	$V_{DRM} \le 800 \text{ V}$	dl/dt	$T_J = T_J$ maximum, $V_{DM} = Rated V_{DRM}$	180	A/μs
	$V_{DRM} \le 1000 \text{ V}$	di/dt	Gate pulse = 20 V, 15 $\Omega$ , $t_p$ = 6 $\mu$ s, $t_r$ = 0.1 $\mu$ s maximum $t_{TM}$ = (2 x rated dl/dt) A	160	
	$V_{DRM} \le 1600 \text{ V}$	' ',	150		
Typical turn-on time		t <sub>gt</sub>	$T_J = 25$ °C, at rated $V_{DRM}/V_{RRM}$ , $T_J = 125$ °C	0.9	
Typical reverse recovery time		t <sub>rr</sub>	$T_J = T_J$ maximum, $I_{TM} = I_{T(AV)}$ , $t_p > 200 \mu s$ , $dI/dt = -10 A/\mu s$	4	μs
Typical turn-off time		t <sub>q</sub>	$\begin{split} T_J = T_J &\text{ maximum, } I_{TM} = I_{T(AV)},  t_p > 200  \mu\text{s, } V_R = 100 \text{ V}, \\ &\text{dI/dt} = \text{-} 10 \text{ A/}\mu\text{s, } \text{dV/dt} = 20 \text{ V/}\mu\text{s linear to 67 } \% \text{ V}_{DRM}, \\ &\text{gate bias 0 V to 100 W} \end{split}$	110	μΟ

#### Note

•  $t_q = 10 \mu s$  up to 600 V,  $t_q = 30 \mu s$  up to 1600 V available on special request

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise	dV/dt	T <sub>J</sub> = T <sub>J</sub> maximum linear to 100 % rated V <sub>DRM</sub>	100	V/µs
of off-state voltage	av/at	T <sub>J</sub> = T <sub>J</sub> maximum linear to 67 % rated V <sub>DRM</sub>	300 (1)	ν/μ5

#### Note

(1) Available with:  $dV/dt = 1000 V/\mu s$ , to complete code add S90 i.e. 25RIA120S90



TRIGGERING					
PARAMETER	SYMBOL	TES	CONDITIONS	VALUES	UNITS
Maximum peak gate power	P <sub>GM</sub>	T - T maximum		8.0	W
Maximum average gate power	P <sub>G(AV)</sub>	$T_J = T_J$ maximum		2.0	
Maximum peak positive gate current	I <sub>GM</sub>	$T_J = T_J$ maximum		1.5	Α
Maximum peak negative gate voltage	-V <sub>GM</sub>	$T_J = T_J$ maximum		10	V
		T <sub>J</sub> = - 65 °C		90	
DC gate current required to trigger	I <sub>GT</sub>	T <sub>J</sub> = 25 °C	Maximum required gate trigger current/voltage are the lowest value which will trigger all units	60	mA
		T <sub>J</sub> = 125 °C		35	
	V <sub>GT</sub>	T <sub>J</sub> = - 65 °C		3.0	V
DC gate voltage required to trigger		T <sub>J</sub> = 25 °C	6 V anode to cathode applied	2.0	
		T <sub>J</sub> = 125 °C		1.0	
DC gate current not to trigger	I <sub>GD</sub>	$T_J = T_J$ maximum, $V_E$	T <sub>J</sub> = T <sub>J</sub> maximum, V <sub>DRM</sub> = Rated value		mA
DC gate voltage not to trigger	$V_{GD}$	$T_J = T_J$ maximum, $V_{DRM} = Rated value$	Maximum gate current/voltage not to trigger is the maximum value which will not trigger any unit with rated V <sub>DRM</sub> anode to cathode applied	0.2	V

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-65 to +125	°C	
Maximum thermal resistance, junction to case	R <sub>thJC</sub>	DC operation	0.75	K/W	
Maximum thermal resistance, case to heat sink	R <sub>thCS</sub>	Mounting surface, smooth, flat and greased 0.35		- r\vv	
Allowable mounting torque		Non-lubricated threads	3.4 + 0 - 10 % (30)	N⋅m	
Allowable mounting torque		Lubricated threads	2.3 + 0 - 10 % (20)	(lbf · in)	
Approximate weight			14	g	
Approximate weight			0.49	OZ.	
Case style		See dimensions - link at the end of datasheet	TO-208AA	(TO-48)	

△R <sub>thJC</sub> CONDUCTION				
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS
180°	0.17	0.13		
120°	0.21	0.22		
90°	0.27	0.30	$T_J = T_J$ maximum	K/W
60°	0.40	0.42		
30°	0.69	0.70		

#### Note

The table above shows the increment of thermal resistance R<sub>thJC</sub> when devices operate at different conduction angles than DC

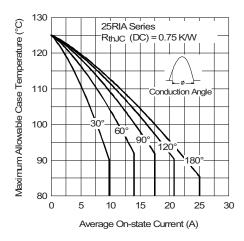


Fig. 1 - Current Ratings Characteristics

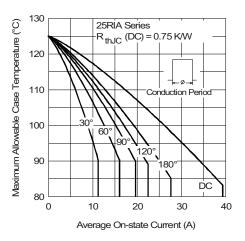


Fig. 1 - Current Ratings Characteristics

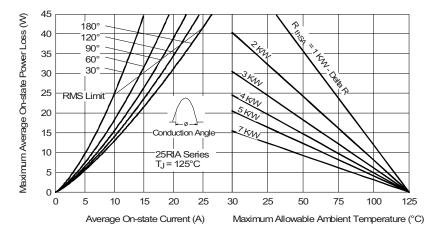


Fig. 2 - On-State Power Loss Characteristics

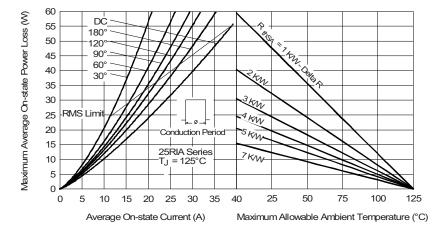


Fig. 3 - On-State Power Loss Characteristics



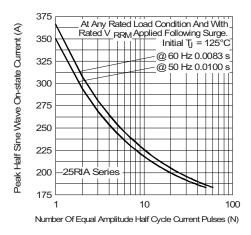


Fig. 4 - Maximum Non-Repetitive Surge Current

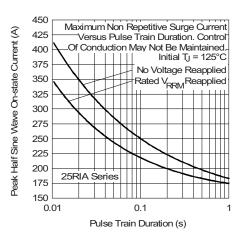


Fig. 5 - Maximum Non-Repetitive Surge Current

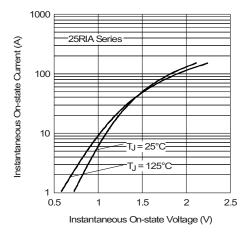


Fig. 6 - Forward Voltage Drop Characteristics

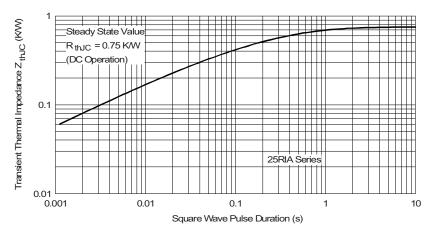


Fig. 7 - Thermal Impedance Z<sub>thJC</sub> Characteristics



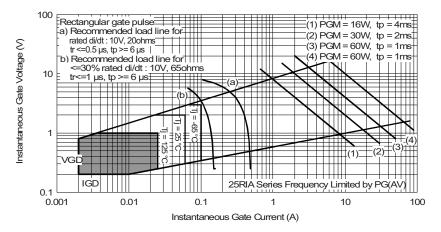
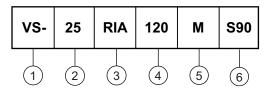


Fig. 8 - Gate Characteristics

#### **ORDERING INFORMATION TABLE**

Device code



1 - Vishay Semiconductors product

2 - Current code

3 - Essential part number

- Voltage code x 10 = V<sub>RRM</sub> (see Voltage Ratings table)

None = stud base TO-208AA (TO-48) 1/4" 28UNF-2A
M = stud base TO-208AA (TO-48) M6 x 1

6 - Critical dV/dt:

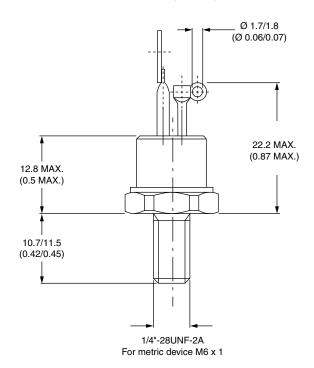
None = 300 V/µs (standard value) S90 = 1000 V/µs (special selection)

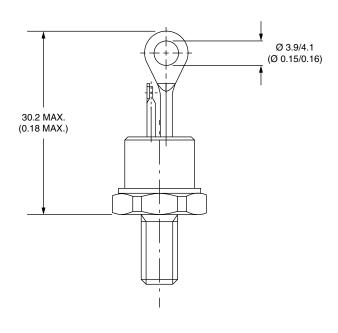
	LINKS TO RELATED DOCUMENTS
Dimensions	www.vishay.com/doc?95333

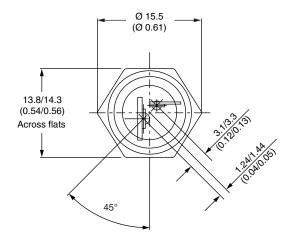


# TO-208AA (TO-48)

### **DIMENSIONS** in millimeters (inches)









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